

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device includes a process of forming a gate electrode having a metallic silicide layer on a semiconductor substrate, a process of decreasing boundaries of grains on the surface of the metallic silicide layer, at least a portion of which is exposed, and a process of forming spacers comprising an oxide film on the side wall of the gate electrode; in this order. Thus, abnormal oxidation of the metallic silicide layer is avoided.